

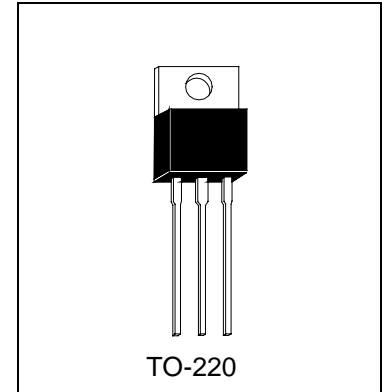


# H2N6668

PNP EPITAXIAL PLANAR TRANSISTOR

## Description

The H2N6668 is designed for general-purpose amplifier and switching applications.



## Absolute Maximum Ratings (T<sub>A</sub>=25°C)

- Maximum Temperatures
  - Storage Temperature ..... -55~+150°C
  - Junction Temperature ..... +150°C Maximum
- Maximum Power Dissipation
  - Total Power Dissipation (T<sub>C</sub>=25°C) ..... 65 W
- Maximum Voltages and Currents
  - BV<sub>CBO</sub> Collector to Base Voltage ..... -80 V
  - BV<sub>CEO</sub> Collector to Emitter Voltage ..... -80 V
  - BV<sub>EBO</sub> Emitter to Base Voltage ..... -5 V
  - I<sub>C</sub> Collector Current ..... -10 A

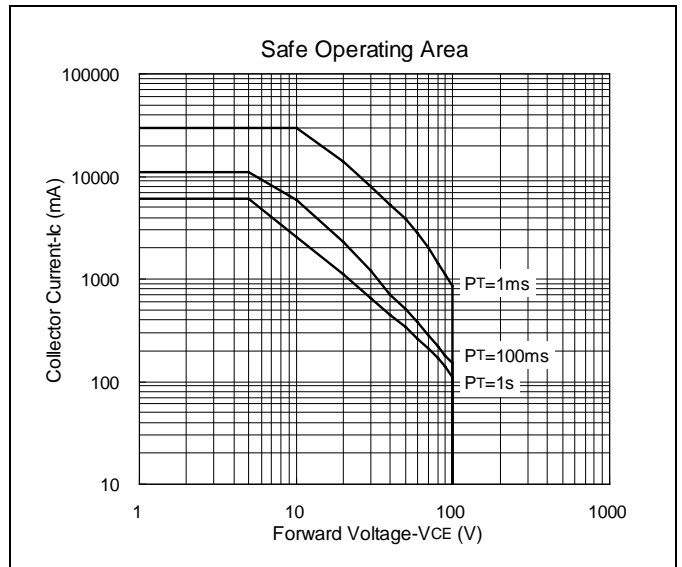
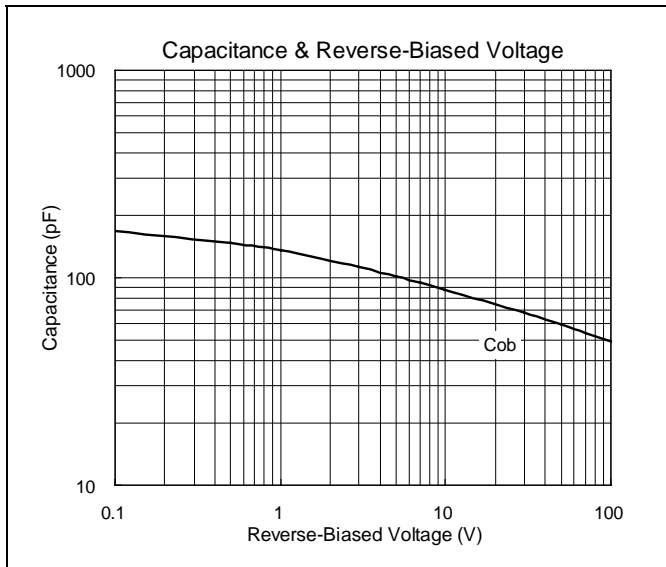
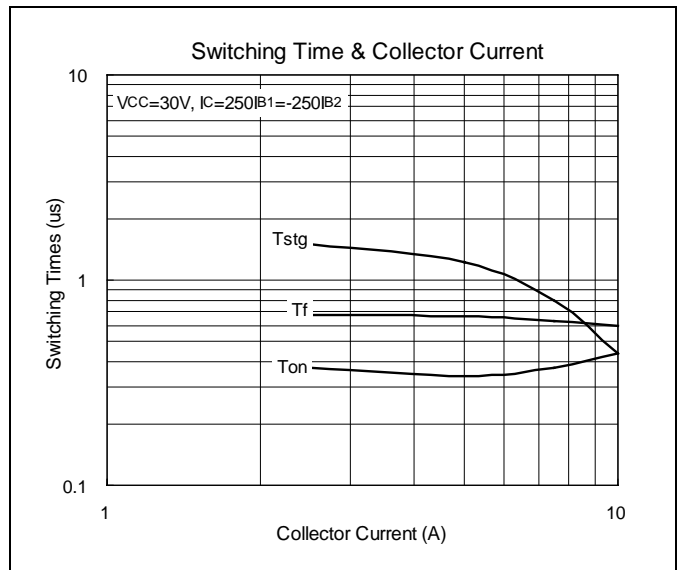
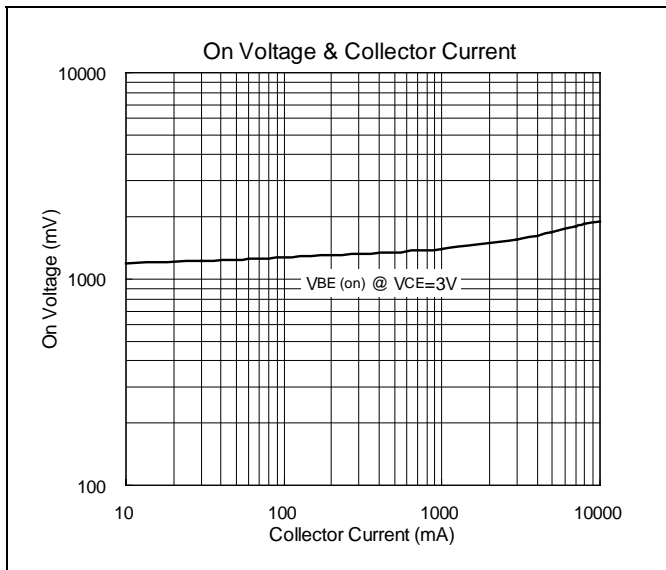
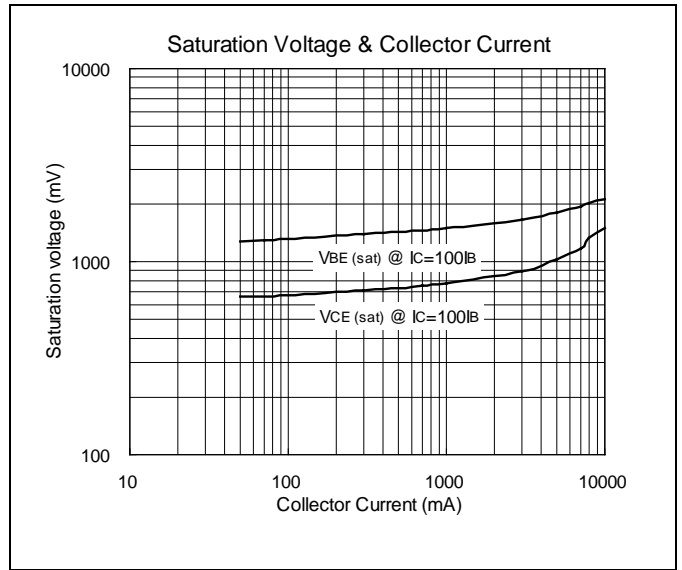
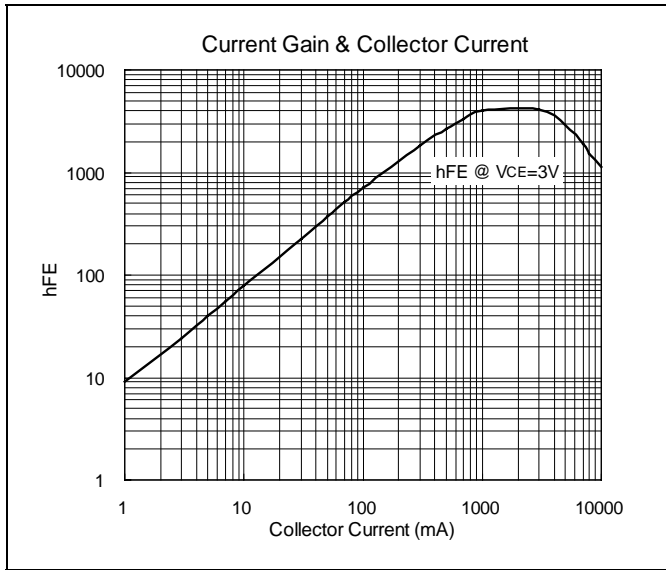
## Electrical Characteristics (T<sub>A</sub>=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	-80	-	-	V	I <sub>C</sub> =-10mA
I <sub>EBO</sub>	-	-	-100	mA	V <sub>EB</sub> =-5V
I <sub>CEO</sub>	-	-	-1	mA	V <sub>CE</sub> =-80V
I <sub>CEV</sub>	-	-	-300	uA	V <sub>CE</sub> =-80V, V <sub>BE(off)</sub> =-1.5V
*V <sub>CE(sat)1</sub>	-	-	-2	V	I <sub>C</sub> =-5A, I <sub>B</sub> =-10mA
*V <sub>CE(sat)2</sub>	-	-	-3	V	I <sub>C</sub> =-10A, I <sub>B</sub> =-100mA
V <sub>BE(on)1</sub>	-	-	-2.8	V	I <sub>C</sub> =-5A, V <sub>CE</sub> =-3V
V <sub>BE(on)2</sub>	-	-	-4.5	V	I <sub>C</sub> =-10A, V <sub>CE</sub> =-3V
*h <sub>FE1</sub>	1	-	20	K	I <sub>C</sub> =-5A, V <sub>CE</sub> =-3V
*h <sub>FE2</sub>	100	-	-		I <sub>C</sub> =-10A, V <sub>CE</sub> =-3V

\*Pulse Test: Pulse Width ≤380us, Duty Cycle ≤2%



### Characteristics Curve





### TO-220AB Dimension

3-Lead TO-220AB  
 Plastic Package  
 HSMC Package Code: E

**Marking:**

Pb Free Mark  
 Pb-Free: "•" (Note)  
 Normal: None

Date Code      Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Base 2.Collector 3.Emitter

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	5.58	7.49
B	8.38	8.90
C	4.40	4.70
D	1.15	1.39
E	0.35	0.60
F	2.03	2.92
G	9.66	10.28
H	-	*16.25
I	-	*3.83
J	3.00	4.00
K	0.75	0.95
L	2.54	3.42
M	1.14	1.40
N	-	*2.54
O	12.70	14.27
P	14.48	15.87

\*: Typical, Unit: mm

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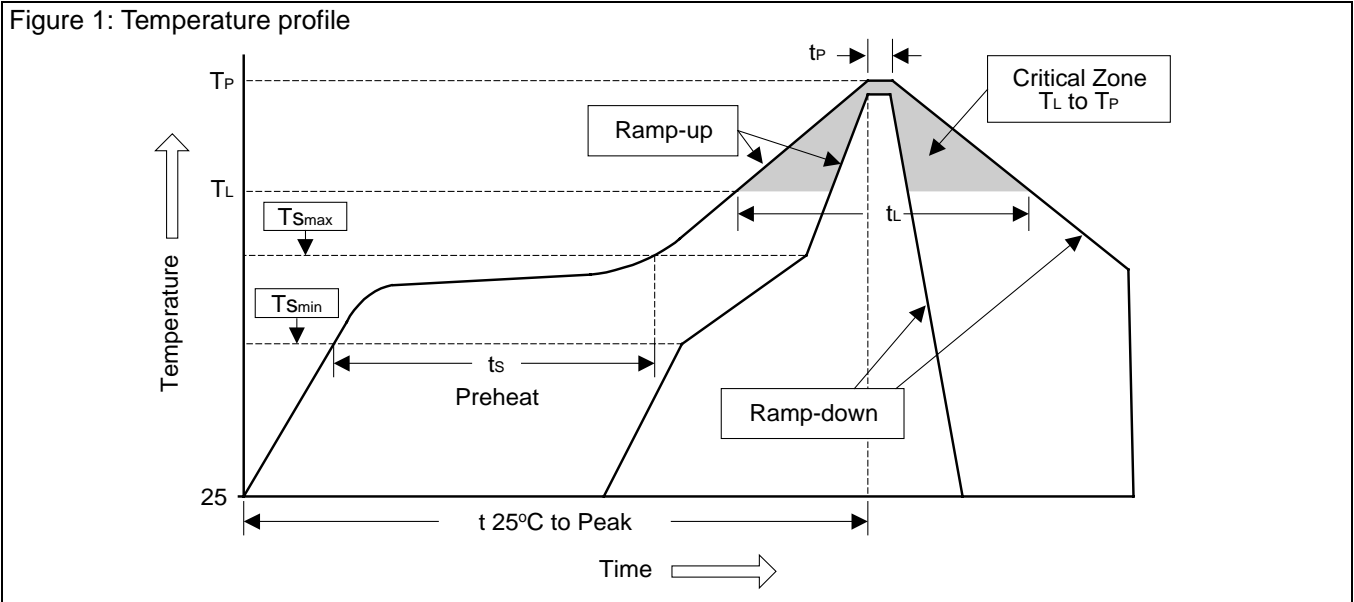
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### Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min ( $T_{Smin}$ )	100°C	150°C
- Temperature Max ( $T_{Smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60~120 sec	60~180 sec
$T_{Smax}$ to $T_L$		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60~150 sec	60~150 sec
Peak Temperature ( $T_P$ )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec